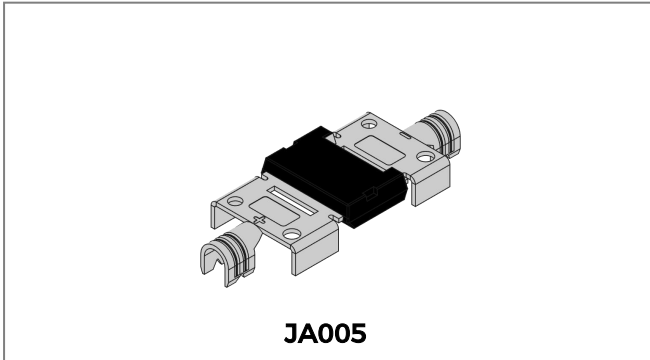


GFJ6145TC Power Schottky Module Bypass Diode



Features

- Trench MOS Schottky technology
- Low thermal resistance
- Lower forward voltage drop, low power loss
- Isolate Package design, ideal for heat dispersion
- High forward current capability
- Excellent anti-humidity
- Low profile package
- High forward surge capability
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request

Mechanical Data

- Case: JA005
- Terminals: Copper
- High temperature soldering guaranteed
- Heated-tool welding 260°C, 10seconds
- Marking Code: GFJ6145TC

Maximum Ratings (limiting values, at 25 °C unless otherwise specified)

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	-	45	V
Average Rectified Forward Current	$I_{F(AV)}$	$T_C = 96^\circ\text{C}$, In DC	60	A
Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3 ms, half Sine pulse	450	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V_{F1}	@ 60A, Pulse, $T_J = 25^\circ\text{C}$	0.47	0.6	V
Reverse Current*	I_{R1}	@ $V_R = \text{rated } V_R$, $T_J = 25^\circ\text{C}$	0.06	0.5	mA
Junction Capacitance	C_T	@ $V_R = 5\text{V}$, $T_C = 25^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$	9835	-	pF

* Pulse width < 300 μs , duty cycle < 2%

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Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	IN DC Forward Mode, without reverse bias, $t \leq 1$ h	-55 to +200	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-	-55 to +150	$^{\circ}\text{C}$
Typical Thermal Resistance Junction to Case	$R_{\theta\text{JC}}$	-	1.0	$^{\circ}\text{C}/\text{W}$

Ratings and Characteristics Curves

Figure 1 Typical Forward Characteristics

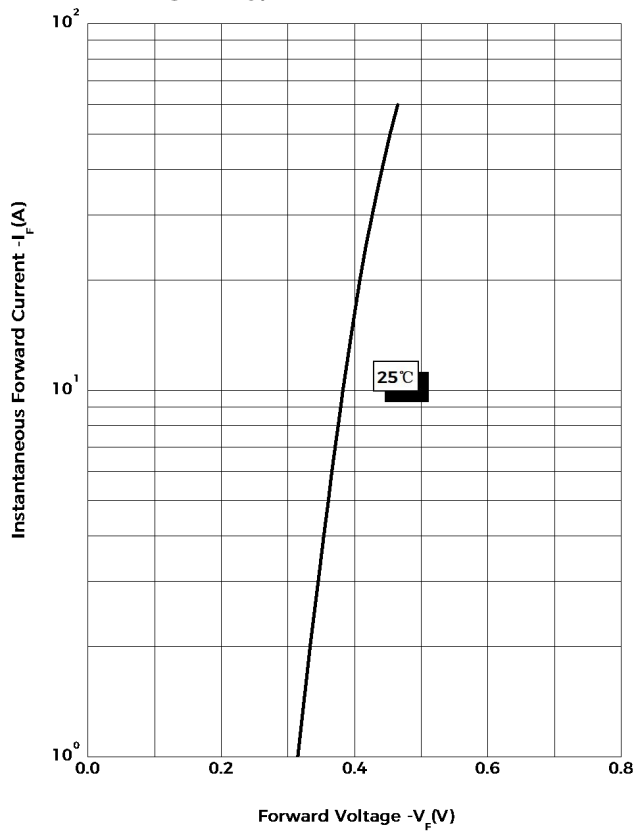


Figure 2 Typical Reverse Characteristics

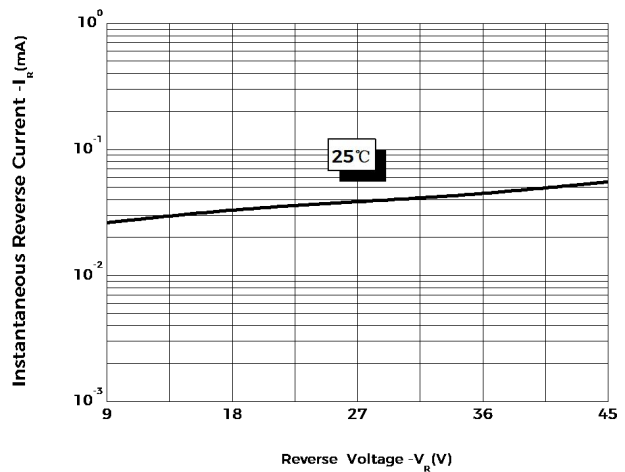
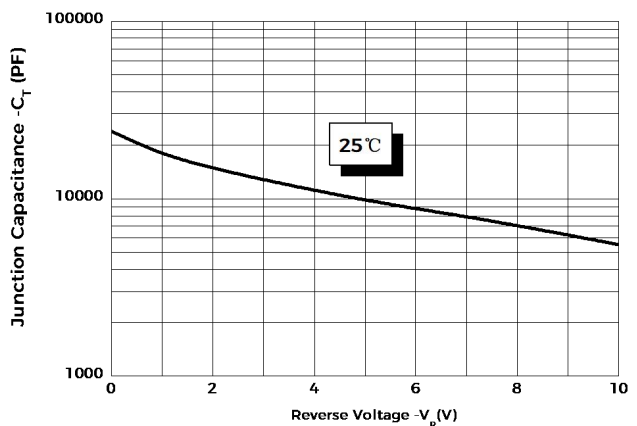


Figure 3 Typical Junction Capacitance

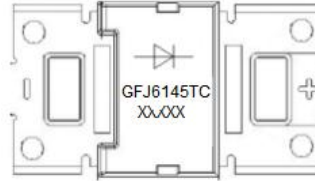


Technical Data
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Ordering Information

Device	Package	Shipping
GFJ6145TC	JA005	30pcs/Tube

Marking Diagram



Where XXXXX is YYWWL

GFJ6145TC = Device Code
YY = Year
WW = Week
L = Lot Number

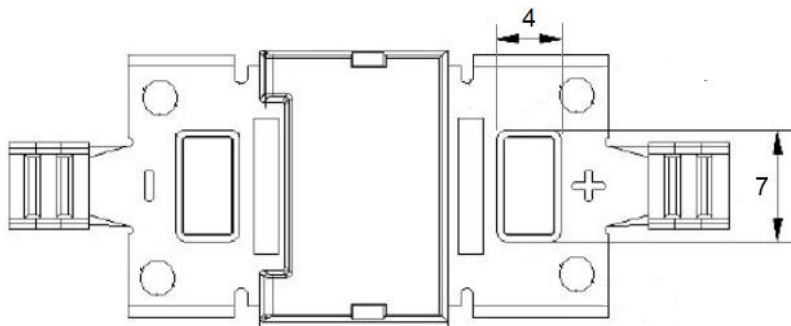
Order P/N	Terminals	Additional
GFJ6145TC-S1	Tin Plated	None
GFJ6145TC-S3	Tin Plated	Solder Block



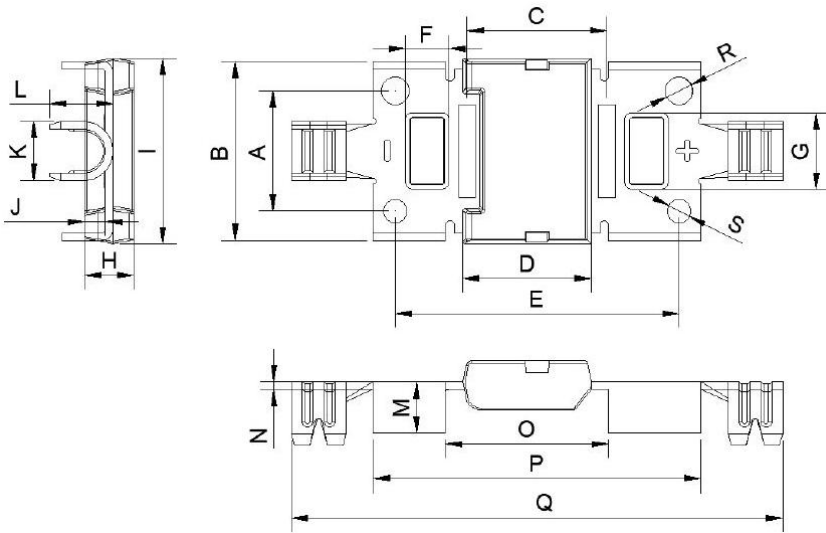
Solder Block

Solder block Specification

The composition of the tin block is Sn50Pb50 with flux.
The size of the tin block is $6(\pm 0.15) \times 3.5(\pm 0.15) \times 1(\pm 0.08)$ mm.
The composition and size of tin blocks can be customized according to customer requirements.
Solder block to be centered, not exceed the flat groove.



Mechanical Dimensions JA005 (Millimeters)



Symbol	Dimensions in millimeters	
	Min.	Max
A	10.5	11.5
B	15.9	16.9
C	12.6	13
D	11.23	12.23
E	25.5	26.5
F	3.5	4.5
G	6.5	7.5
H	4.3	4.7
I	16.5	17.5
J	1.7	2.1
K	5	5.8
L	5.6	6
M	4.4	5
N	0.6	0.8
O	14.73	15.13
P	29.5	30.5
Q	44.5	45.5
R	2.35	2.65
S	2	2.3

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